

**■产品特征**

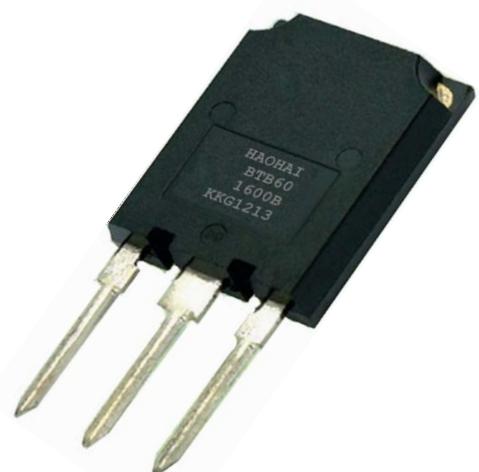
PNPN四层结构硅芯片  
 三象限、三端双向可控硅开关  
 双台面玻璃钝化工艺  
 多层金属化电极提高瞬间浪涌电流承受力  
 较高阻断电压  
 较强抗电流冲击能力

**■应用领域**

自动化电气设备  
 交流/直流电源变换  
 电加热控制  
 无功补偿  
 复合开关  
 大功率捕鱼器  
 电机马达调速控制电路

可代替型号:

BCR30AM-12L  
 30TPS08、30TPS12  
 40TPS08、40TPS12  
 60TPS08、60TPS12  
 TM2561B-L、TM2580B-L  
 TM3561B-L、TM3580B-L  
 TM5561B-L、TM5580B-L  
 TMG25D80L、T25D8L  
 TMG35D80L、T35D8L  
 TMG55D80L、T55D8L



Super-247 or TO-247AA

**■QUICK REFERENCE 【参考特性】**

產品型號 Part Number	工業型號 Industry Part №	通態電流均方值 $I_{TRMS}$ (A)	斷態重復峰值電壓 $V_{DRM} / V_{RRM}$ (V)	門極觸發電流 $I_{GT}$ ( $\mu$ A / mA)	封裝外形 Package	包裝方式 Packing	元件標識 Marking
BTB60-800BW	BTB60-800BW	60 A	800 V	B $\leq 50$ mA	Super-247 TO-247AA	30Pcs/Tube 450Pcs/Box 4.5Kpcs/Box 每管30只 每盒450只 6.5g / Pcs 每枚重量6.5克	H BTB60 1600B KKG1213 H: HAOYI KKG:注册商标 1213:生产日期 2012年第12周出厂 按实际自然周
BTB60-1000BW	BTB60-1000BW		1000 V				
BTB60-1200BW	BTB60-1200BW		1200 V				
BTB60-1400BW	BTB60-1400BW		1400 V				
BTB60-1600BW	BTB60-1600BW		1600 V				
BTB60-1800BW	BTB60-1800BW		1800 V				

- ① 三象限、大电流、高压、特殊机种
- ② 1200V、1600V 常规出货, 其它高压需订制
- ③ 触发电流  $I_{GT}$  值可按客户要求订制

**■PINNING: TO-247AA ( Super-247 ) 【TO-247直插半塑封】【BTB為非絕緣型: 中間管腳T2與散熱片Tab導通】**

Pin 管腳排列	Symbol 對應極性	Description 極性名詞	Description 極性含義	Practicality in Pin Arrange 元件實物與管腳排列	Pin Polarity Circuit diagram 腳位與極性 電路符號表示
1	T1	Main terminal 1	第一陽極	 Tab	1=T1 2=T2 3=G 4=Tab
2	T2	Main terminal 2	第二陽極		
3	G	Gate	門-控制極		
4	Tab	---	散熱片		

**■ ABSOLUTE RATINGS (Limiting Values) 【额定值参数】**

SYMBOL 符號表示	Paramenter & Test Conditions 器件符號含義 及 參數測試條件說明	Value 數值	Unit 單位
I <sub>T(RMS)</sub>	通態電流均方值: On-State RMS Current ( full sine wave, T <sub>C</sub> =75°C)	60	A
I <sub>TSM</sub>	通態浪湧電流 Non repetitive surge peak on-state current	t <sub>p</sub> =10ms, f=50Hz	
		t <sub>p</sub> =8.3ms, f=60Hz	
I <sub>GM</sub>	控制極峰值散耗電流: Peak gate current	t <sub>p</sub> =20μs, T <sub>C</sub> =125°C	8
I <sup>2</sup> t	週期電流平方時間積: I <sup>2</sup> t Value for Fusing Consideration	t <sub>p</sub> =10mS	1800 A <sup>2</sup> ses
P <sub>GM</sub>	控制極峰值散耗功率: Peak gate power	t <sub>p</sub> =20μs, T <sub>C</sub> =125°C	10
P <sub>G(AV)</sub>	門極平均散耗功率: Average gate power dissipation	T <sub>j</sub> =125°C	2
V <sub>DRM</sub>	斷態重複峰值電壓: Repetitive peak off-state voltages	T <sub>j</sub> =25°C 參考型號對照列表	800~1800
V <sub>RRM</sub>	反向重複峰值電壓: Repetitive peak off-state voltages		
T <sub>j</sub>	工作結溫: Operating Junction Temperature Range	@ Rate V <sub>RRM</sub> and V <sub>DRM</sub>	-40 ~ +125
T <sub>stg</sub>	貯存溫度: Storage Temperature Range		-40 ~ +150
T <sub>L</sub>	引腳承受焊錫極限溫度: Maximum Lead Temperature for Soldering Purposes 1/8 from Case for 10 Seconds		260

**■ ELECTRICAL CHARACTERISTICS (T<sub>j</sub>=25°C Unless Otherwise Noted) 【電参数】**

SYMBOL 符號表示	Paramenter & Test Conditions 符號含義 及 參數測試條件 說明	Value			Unit 單位
		最小值	典型值	最大值	
I <sub>GT</sub>	門極觸發電流: Gate trigger current V <sub>D</sub> =12V <sub>DC</sub> , R <sub>L</sub> =33Ω, T <sub>j</sub> =25°C	I - II - III	→	→	50
I <sub>H</sub>	維持電流: Holding Current	I <sub>T</sub> =100mA	→	→	60
I <sub>L</sub>	擎柱電流 Latching Current (I <sub>G</sub> =1.2 I <sub>GT</sub> )	I - III	→	→	80
		II	→	→	100
I <sub>DRM</sub> I <sub>RRM</sub>	斷態重複峰值電流 Latching Current (V <sub>D</sub> =V <sub>DRM</sub> , V <sub>R</sub> =V <sub>DRM</sub> )	T <sub>j</sub> =25°C	→	→	50
		T <sub>j</sub> =125°C	→	→	800
V <sub>GT</sub>	門極觸發電壓: Gate trigger voltage (V <sub>D</sub> =12V <sub>DC</sub> , R <sub>L</sub> =33Ω, T <sub>j</sub> =25°C)	I - II - III	→	→	1.3
V <sub>GD</sub>	門極不觸發電壓: Gate NO-trigger voltage (V <sub>D</sub> =V <sub>DRM</sub> , R <sub>L</sub> =33Ω, T <sub>j</sub> =25°C)	I - II - III	0.2	←	←
V <sub>TM</sub>	通態峰值電壓: Peak Forward On-State Voltage	I <sub>TM</sub> =90A, t <sub>p</sub> =380μs, T <sub>j</sub> =25°C	→	→	1.55
dV/dt	斷態臨界電壓上升率: Critical Rate of Rise of Off-State Voltage	V <sub>D</sub> =67%V <sub>DRM</sub> gate open T <sub>j</sub> =125°C	1000	←	←
(di/dt)c	通態臨界電流上升率: Critical Rate of Rise of On-State Current	Without sunubber T <sub>j</sub> =125°C	20	←	←
R <sub>th(j-c)</sub>	熱阻-結到外殼: Thermal Resistance-Junction-to-Case	→	0.45	←	°C/W
R <sub>th(j-a)</sub>	熱阻-結到環境: Thermal Resistance-Junction-to-Ambient	→	40	←	

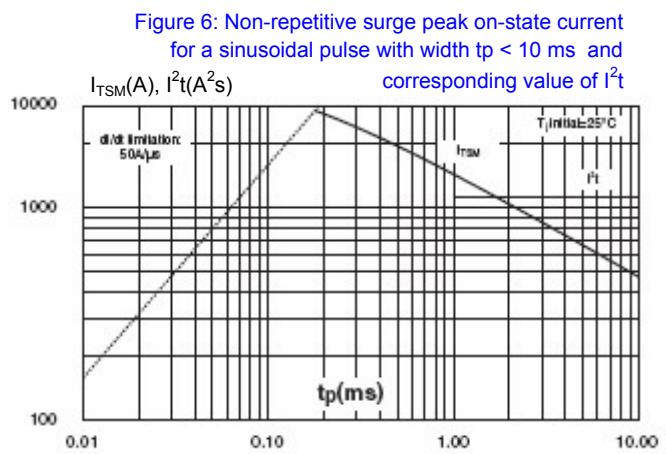
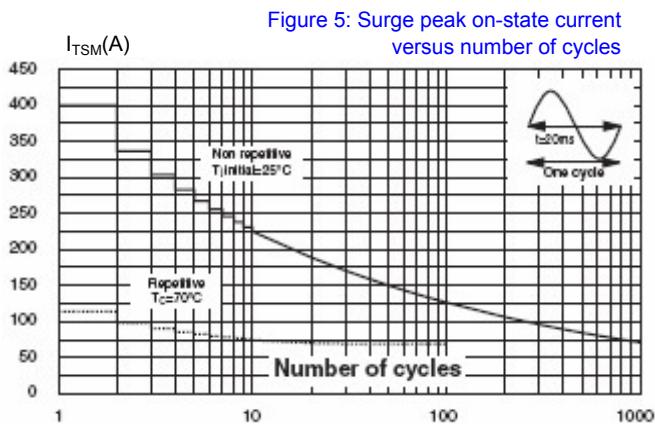
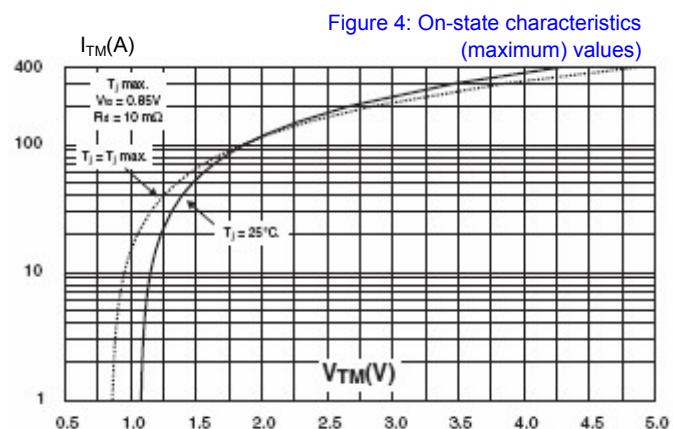
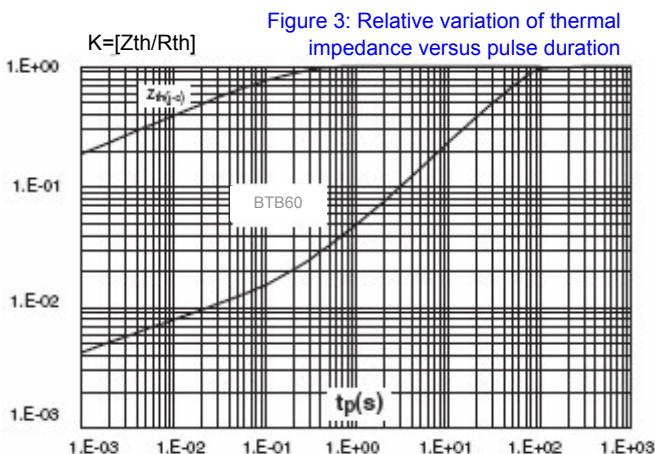
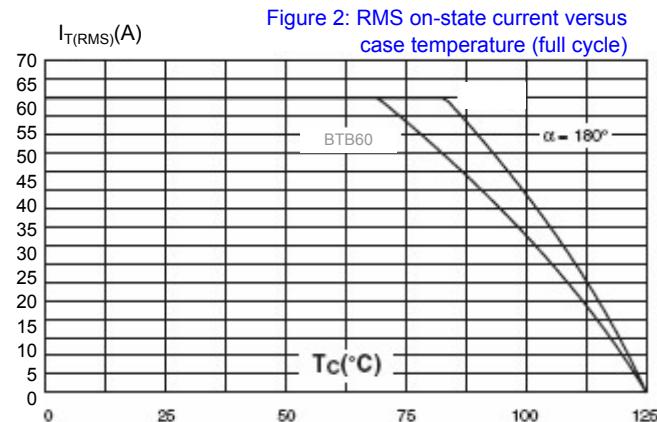
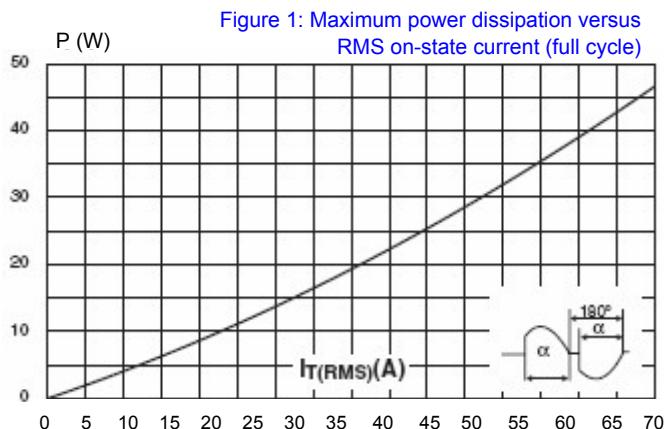


Figure 7: Relative variation of gate trigger current, holding current and latching current versus junction temperature  
(typical values)

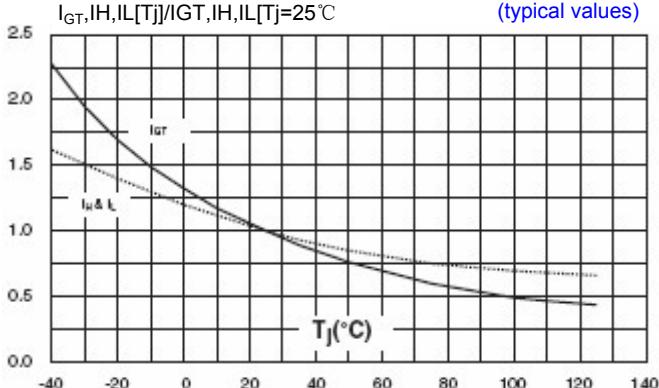


Figure 8: Relative variation of critical rate of decrease of main current versus (dV/dt)c  
(typical values)

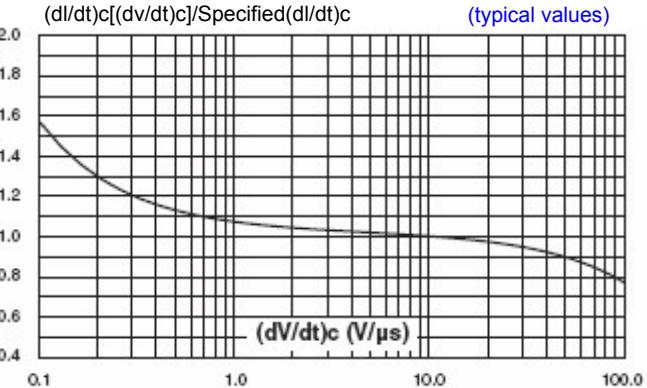


Figure 9: Relative variation of critical rate of decrease of main current versus (dV/dt)c  
(dI/dt)c[Tj]/(dI/dt)c[T] specified]

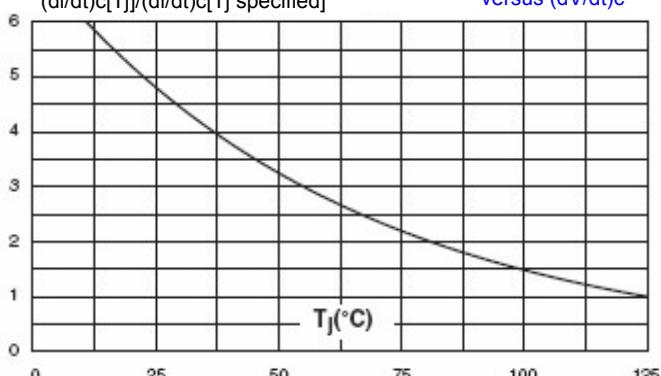
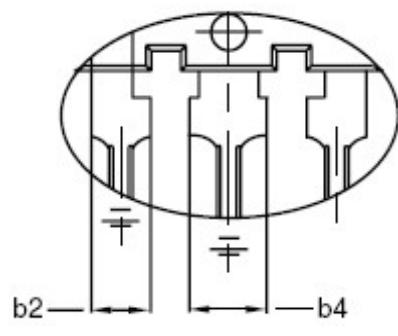
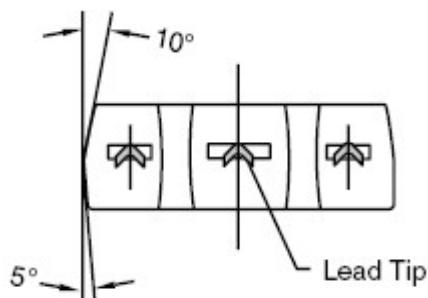
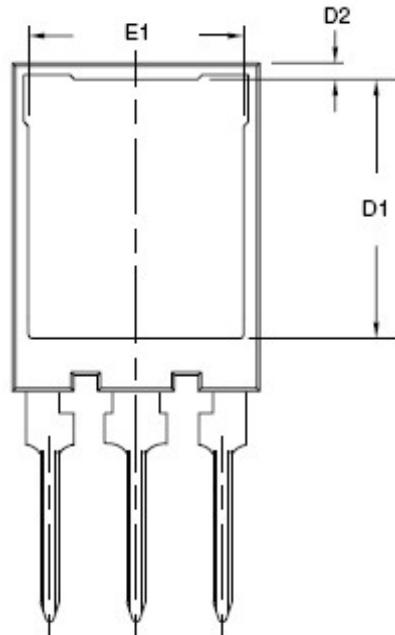
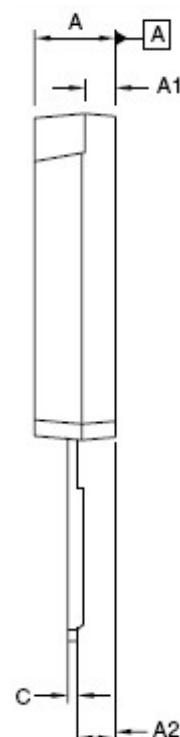
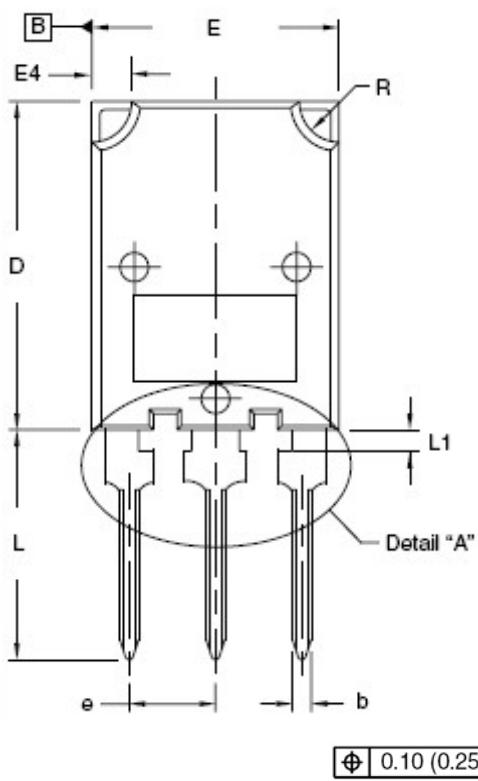


Figure 10: Component physical picture



**Package Information (mm & Inches)**

TO-247AA (Super-247) 封裝尺寸 單位: 毫米與英寸對照 mm &amp; Inches



Detail "A"      Scale: 2:1

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.70	5.30	0.185	0.209
A1	1.50	2.50	0.059	0.098
A2	2.25	2.65	0.089	0.104
b	1.30	1.60	0.051	0.063
b2	1.80	2.20	0.071	0.087
b4	3.00	3.25	0.118	0.128
c	0.80	1.20	0.031	0.047
D	19.80	20.80	0.780	0.819

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	15.50	16.10	0.610	0.634
D2	0.700	1.300	0.028	0.051
E	15.10	16.10	0.594	0.634
E1	13.30	13.90	0.524	0.547
e	5.45 BSC		0.215 BSC	
L	13.70	14.70	0.539	0.579
L1	1.000	1.600	0.039	0.063
R	2.000	3.000	0.079	0.118

KKG @ HAOHAI Product Database 2009-04-02 HV.8-1.5

KKG @ HAOHAI Product Database 2012-05-01 HV.8-2.0



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